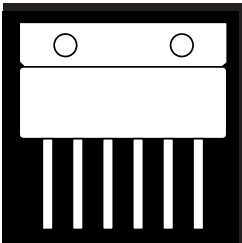


INSULATED GATE BIPOLAR TRANSISTOR (IGBT) IN A HERMETIC ISOLATED SIP PACKAGE



1000 Volt, 25 Amp, N-Channel IGBT
In A Hermetic Metal Package

FEATURES

- Two Isolated IGBTs In A Hermetic SIP Package
- High Input Impedance
- Low On-Voltage
- High Current Capability
- High Switching Speed
- Low Tail Current
- Available With Free Wheeling Diodes
- Available Screened To MIL-S-19500, TX, TXV And S Levels

DESCRIPTION

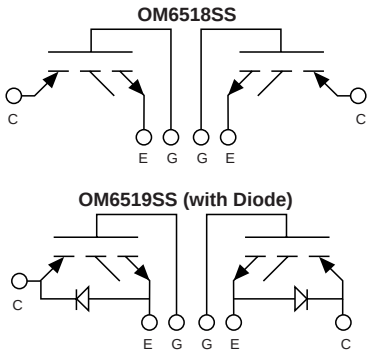
This IGBT power transistor features the high switching speeds of a power MOSFET and the low on-resistance of a bipolar transistor. It is ideally suited for high power switching applications such as frequency converters for 3Ø motors, UPS and high power SMPS.

MAXIMUM RATINGS @ 25°C Unless Specified Otherwise

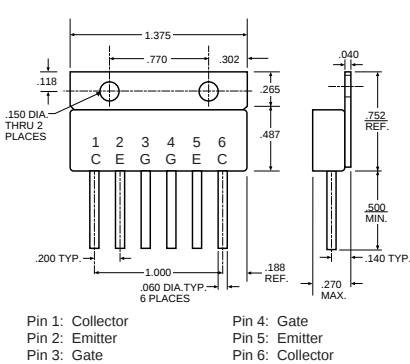
PART NUMBER	I _C (Cont.) @ 90°C, A	V _{(BR)CES} V	V _{CE (sat)} (Typ.) V	T _f (Typ.) ns	q _{JC} °C/W	P _D W	T _J °C
OM6518SS	25	1000	4.0	300	1.0	125	150
OM6519SS	25	1000	4.0	300	1.0	125	150

3.1

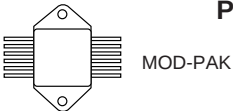
SCHEMATIC



MECHANICAL OUTLINE



PACKAGE OPTIONS



IGBTs are also available in Z-Tab, dual and quad pak styles -
Please call the factory for more information.